Product data sheet

1. General description

N-channel enhancement mode field-effect transistor in a plastic package using TrenchMOS technology.

2. Features and benefits

Low on-state resistance in a small surface mount package

3. Applications

DC-to-DC primary side switching

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DS}	drain-source voltage	25 °C < T _j < 150 °C	-	-	100	V
V _{GS}	gate-source voltage	T _j = 25 °C	-30	-	30	V
I _D	drain current	V _{GS} = 10 V; T _{sp} = 25 °C	-	-	1.9	Α
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 0.5 \text{ A}; T_j = 25 \text{ °C}$	-	213	250	mΩ
P _{tot}	total power dissipation	T _{sp} = 25 °C	-	-	2	W



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	3	D _.
2	S	source		
3	D	drain		G (F)
			1 2	mbb076 S
			SOT23	

6. Ordering information

Table 3. Ordering information

Type number Package						
	Name	Description	Version			
PMV213SN	SOT23	plastic, surface-mounted package; 3 terminals; 1.9 mm pitch; 2.9 mm x 1.3 mm x 1 mm body	SOT23			

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PMV213SN	%2N

[1] % = placeholder for manufacturing site code

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Mir	n Max	Unit
V _{DS}	drain-source voltage	25 °C < T _j < 150 °C	-	100	V
V_{DGR}	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega; 25 \text{ °C} < T_j < 150 \text{ °C}$	-	100	V
V_{GS}	gate-source voltage	T _j = 25 °C	-30	30	V
I _D	drain current	V _{GS} = 10 V; T _{sp} = 25 °C	-	1.9	Α
		V _{GS} = 10 V; T _{sp} = 100 °C	-	1.2	Α
I _{DM}	peak drain current	T_{sp} = 25 °C; single pulse; $t_p \le 10 \mu s$	-	7.6	А
P _{tot}	total power dissipation	T _{sp} = 25 °C	-	2	W
T _j	junction temperature		-55	150	°C
T _{stg}	storage temperature		-55	150	°C
Source-drain	n diode			·	
Is	source current	T _{sp} = 25 °C	-	1.7	А
I _{SM}	peak source current	single pulse; $t_p \le 10 \mu s$; $T_{sp} = 25 °C$	-	6.9	А

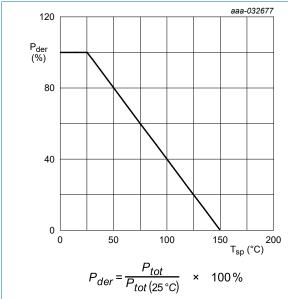


Fig. 1. Normalized total power dissipation as a function of solder point temperature

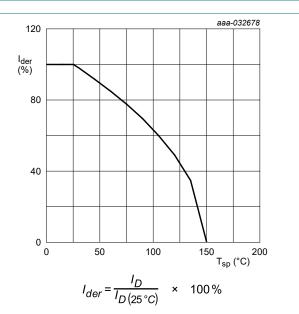
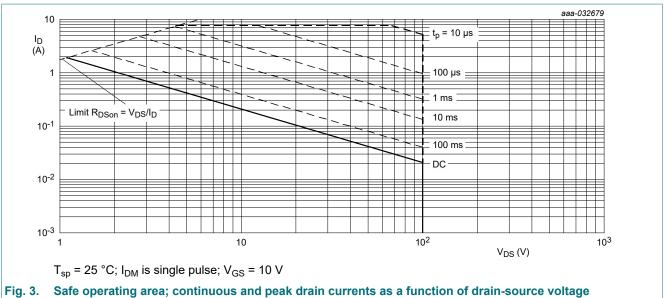


Fig. 2. Normalized continuous drain current as a function of solder point temperature

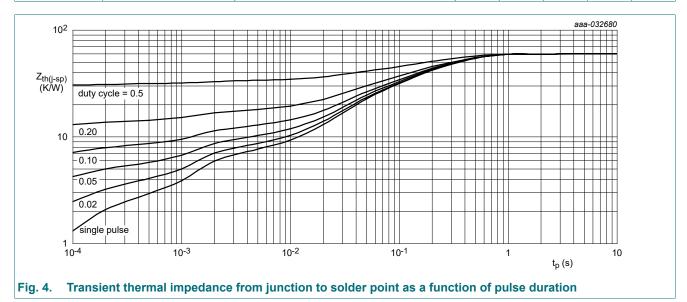


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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-sp)}	thermal resistance from		-	-	60	K/W
	junction to solder point					



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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{(BR)DSS}	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	100	-	-	V
	breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = -55 °C	90	-	-	V
V _{GSth}	gate-source threshold	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	2	3	4	V
	voltage	I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 150 °C	1.2	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}$	-	-	4.4	V
I _{DSS}	drain leakage current	V _{DS} = 100 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μΑ
		V _{DS} = 100 V; V _{GS} = 0 V; T _j = 150 °C	-	-	100	μΑ
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	10	100	nA
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	-10	-100	μΑ
R _{DSon}	drain-source on-state	$V_{GS} = 10 \text{ V}; I_D = 0.5 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	213	250	mΩ
	resistance	V _{GS} = 10 V; I _D = 0.5 A; T _j = 150 °C	-	490	575	mΩ
Q _{G(tot)}	total gate charge	V _{DS} = 80 V; I _D = 1.2 A; V _{GS} = 10 V;	-	7	-	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	1.4	-	nC
Q _{GS(th)}	pre-threshold gate- source charge		-	2.5	-	nC
C _{iss}	input capacitance	V _{DS} = 20 V; f = 1 MHz; V _{GS} = 0 V;	-	330	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	36	-	pF
C _{rss}	reverse transfer capacitance		-	22	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 50 \text{ V}; R_L = 33 \Omega; V_{GS} = 10 \text{ V};$	-	5.5	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 ^{\circ}C$	-	5	-	ns
t _{d(off)}	turn-off delay time		-	9.5	-	ns
t _f	fall time	1	-	3	-	ns
Source-drai	n diode			-		
V _{SD}	source-drain voltage	I _S = 1.5 A; V _{GS} = 0 V; T _j = 25 °C	-	0.83	1.2	V
t _{rr}	reverse recovery time	$I_S = 1.2 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s};$	-	36	-	ns
Q _r	recovered charge	V _{GS} = 0 V; T _j = 25 °C	-	23	-	nC

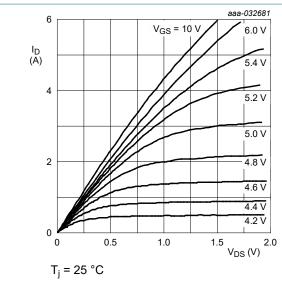


Fig. 5. Output characteristics: drain current as a function of drain-source voltage; typical values

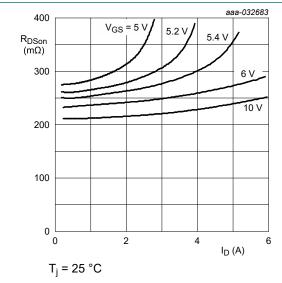
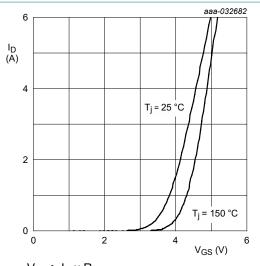


Fig. 7. Drain-source on-state resistance as a function of drain current; typical values



 $V_{DS} > I_D \times R_{DSon}$

Fig. 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values

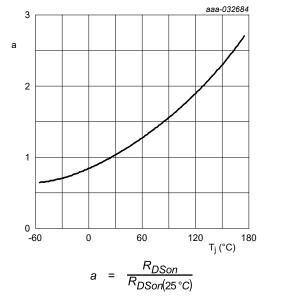


Fig. 8. Normalized drain-source on-state resistance as a function of junction temperature

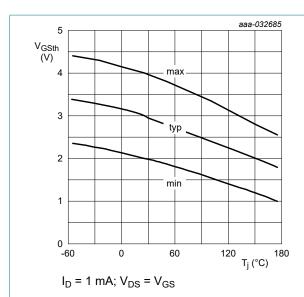


Fig. 9. Gate-source threshold voltage as a function of junction temperature

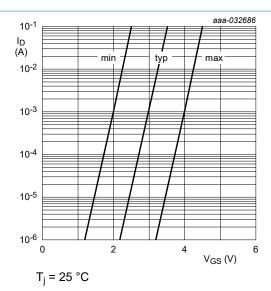


Fig. 10. Subthreshold drain current as a function of gate-source voltage

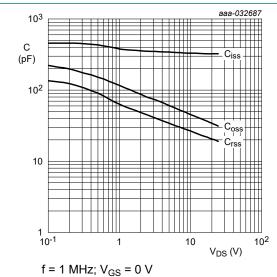
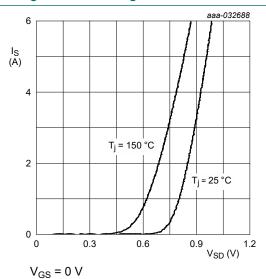
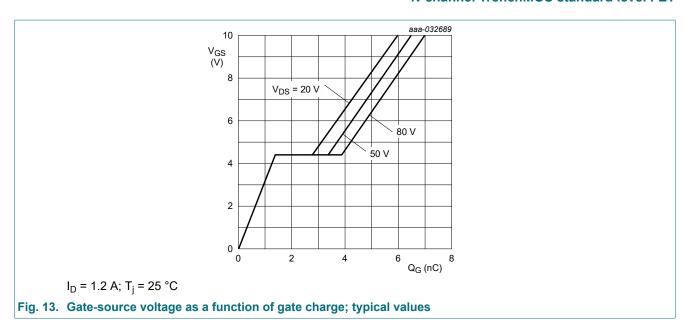


Fig. 11. Input, output and reverse transfer capacitances | Fig. 12. Source (diode forward) current as a function of as a function of drain-source voltage; typical values



source-drain (diode forward) voltage; typical values



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11. Package outline

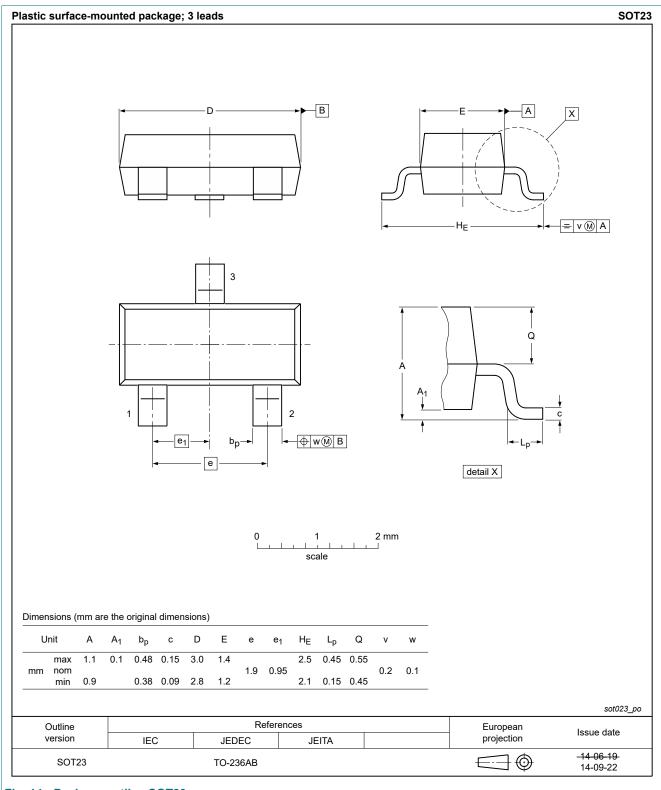
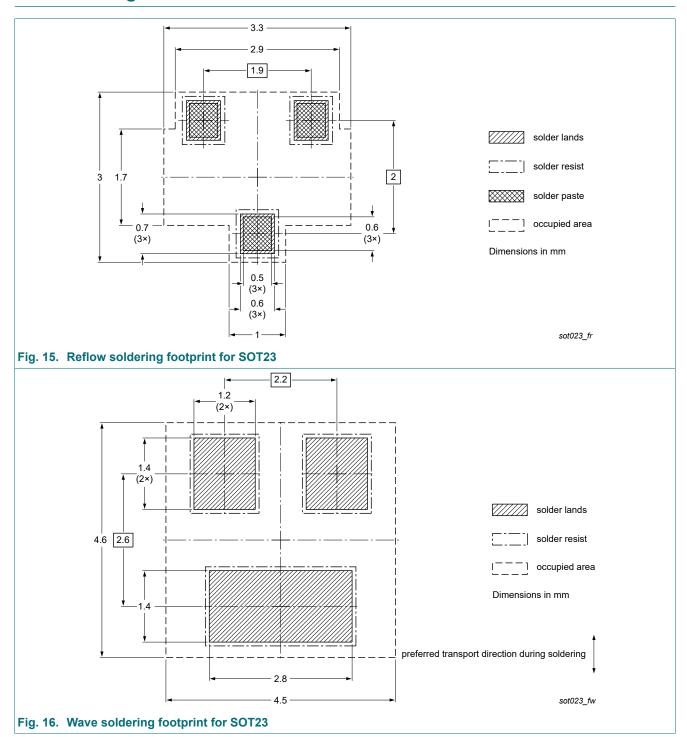


Fig. 14. Package outline SOT23

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12. Soldering



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13. Revision history

Table 8. Revision history

Table of Revision metery							
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
PMV213SN v.3	20201123	Product data sheet	-	PMV213SN v.2			
Modifications:	 The format of this data sheet has been redesigned to comply with the identity guidelines of Nexperia. Legal texts have been adapted to the new company name where appropriate. 						
PMV213SN v.2	20030219	Product data sheet	-	PMV213SN v.1			
PMV213SN v.1	20030115	Product data sheet	-	-			

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14. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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